



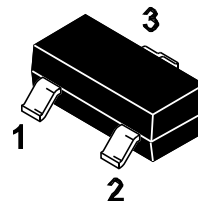
PJM84PSA

P-Channel Enhancement Mode Power MOSFET

Features

- Energy efficient
- Low threshold voltage
- High-speed switching
- ESD protected(HBM) up to 2KV
- Miniature surface mount package saves board space
- $V_{DS} = -20V, I_D = -4A$
 $R_{DS(on)} < 50m\Omega @ V_{GS} = -4.5V$

SOT-23



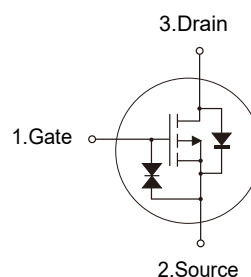
1. Gate 2. Source 3. Drain

Marking Code: P84

Applications

- PWM applications
- Load switch
- Power management

Schematic Diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	$-I_D$	0.13	A
Drain Current-Pulsed ^{Note1} at $t_p < 10\mu s$	$-I_{DM}$	0.52	A
Maximum Power Dissipation	P_D	225	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	556	°C/W
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Electrical Characteristics

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	-V _{(BR)DSS}	V _{GS} =0V,I _D =-250μA	50	--	--	V
Zero Gate Voltage Drain Current	-I _{DSS}	V _{DS} =-50V,V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	--	--	±10	μA
Gate Threshold Voltage ^{Note3}	-V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	0.9	1.6	2	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =-10V,I _D =-0.1A	--	2.5	8	Ω
		V _{GS} =-5V,I _D =-0.1A	--	3	10	Ω
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =-25V,I _D =-0.1A	50	--	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =-5V,V _{GS} =0V,f=1MHz	--	30	--	pF
Output Capacitance	C _{oss}		--	10	--	pF
Reverse Transfer Capacitance	C _{rss}		--	5	--	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-2.5A ,R _L =50Ω	--	2.5	--	nS
Turn-on Rise Time	t _r		--	1	--	nS
Turn-off Delay Time	t _{d(off)}		--	16	--	nS
Turn-off Fall Time	t _f		--	8	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	-V _{SD}	V _{GS} =0V,I _S =-0.13A	--	--	1.2	V
Diode Forward Current ^{Note2}	-I _S		--	--	0.13	A

Note: 1. Repetitive rating : Pulse width limited by junction temperature.

2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

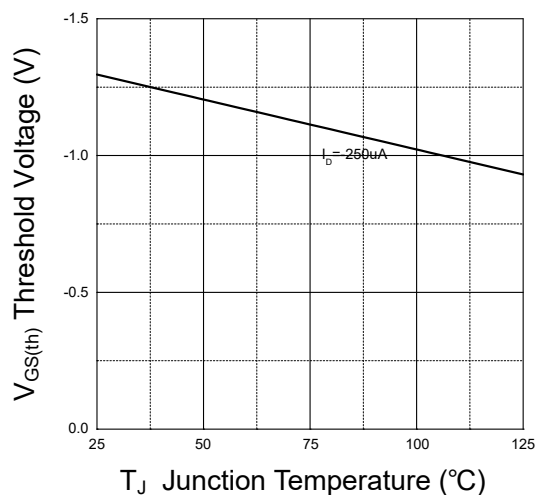
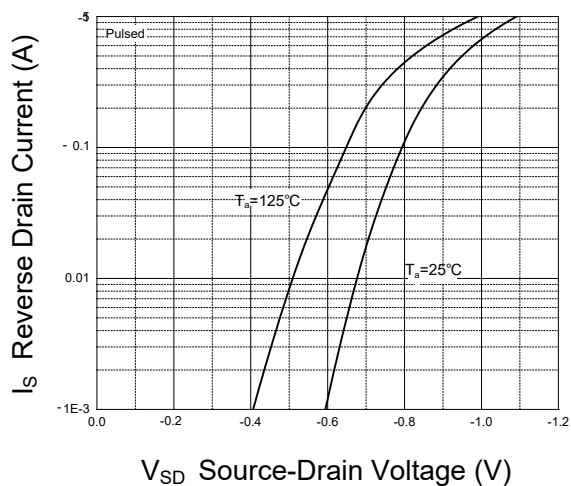
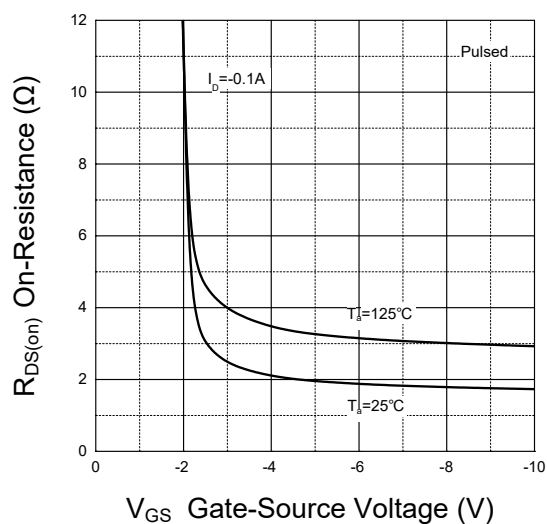
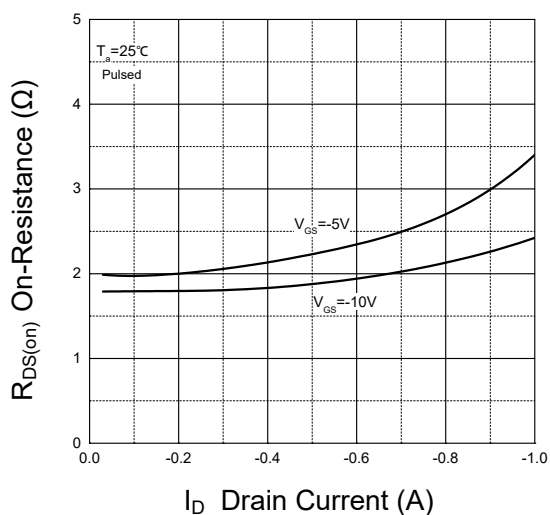
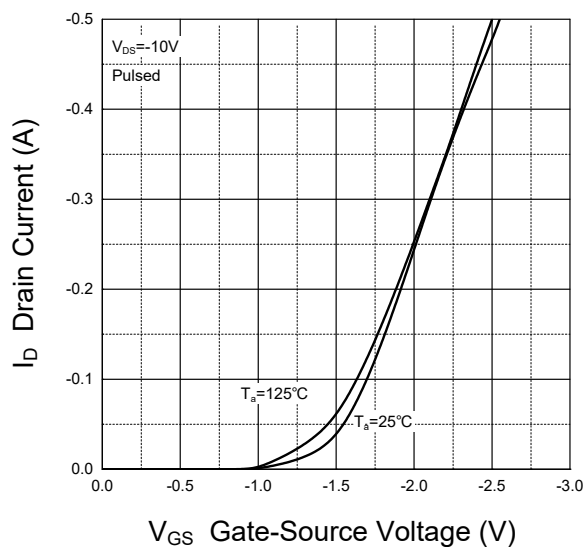
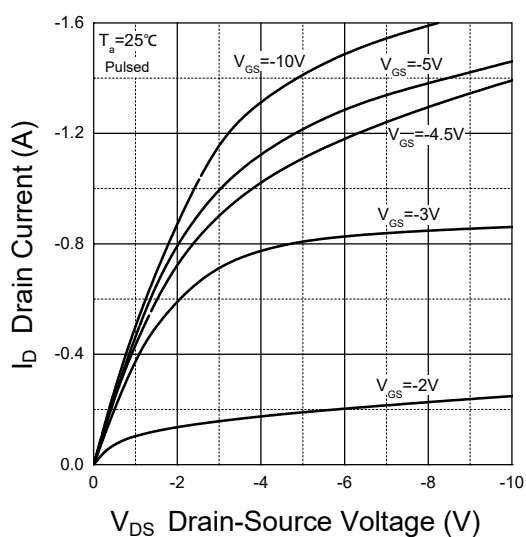
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.



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Typical Characteristic Curves





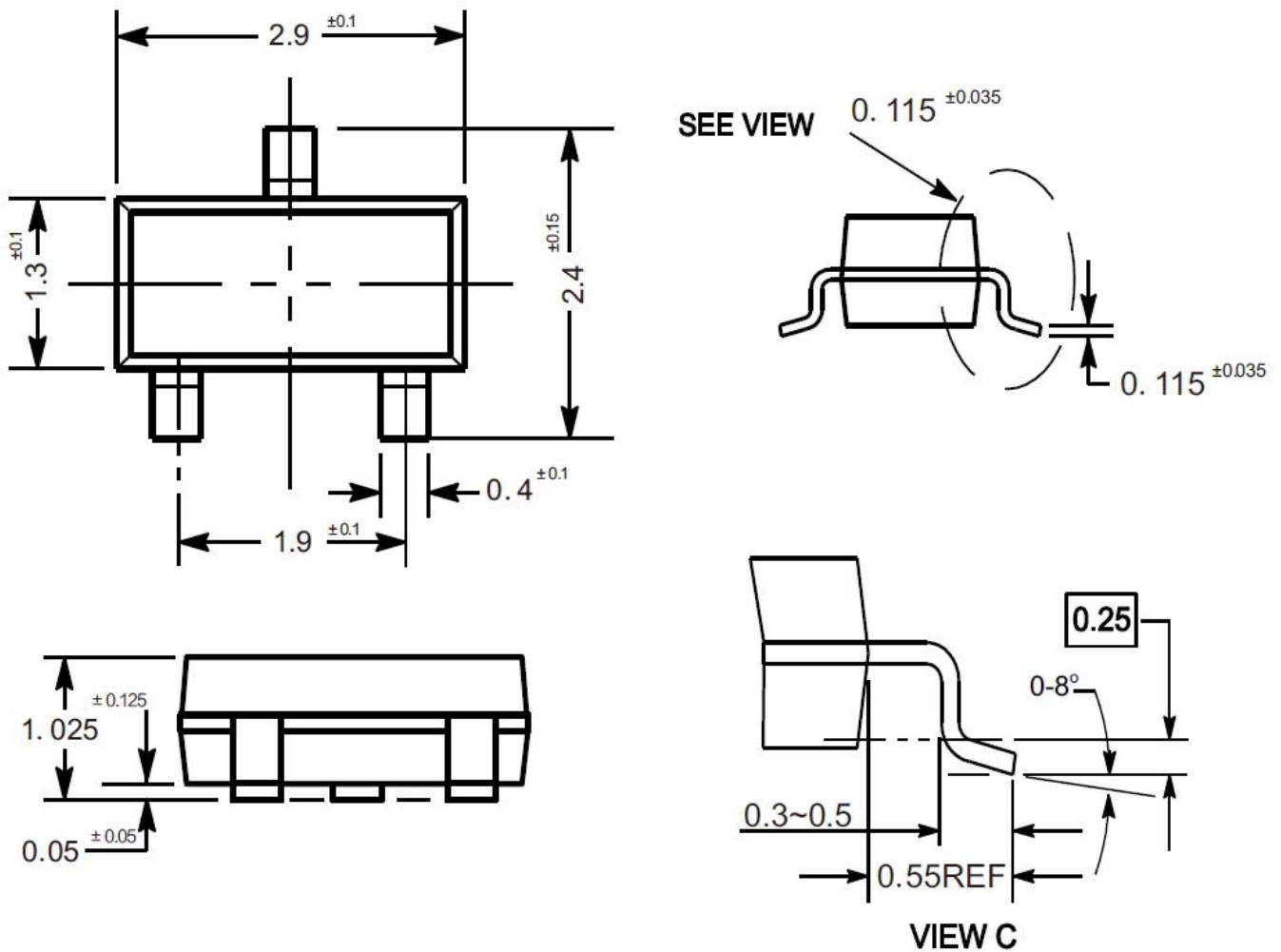
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Package Outline

SOT-23

Dimensions in mm



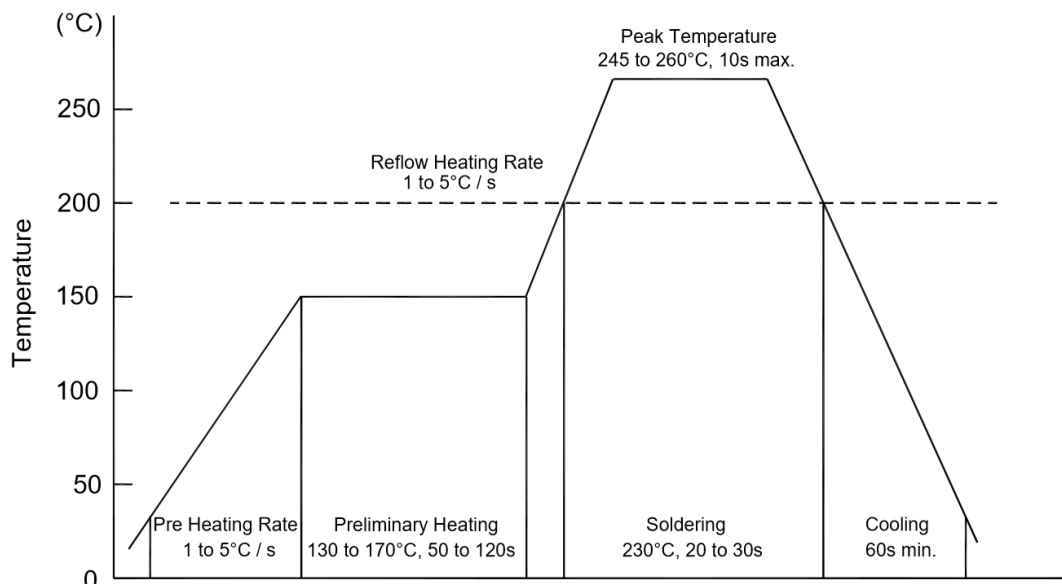
Ordering Information

Device	Package	Shipping
PJM3415PSA	SOT-23	3,000PCS/Reel&7inches



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

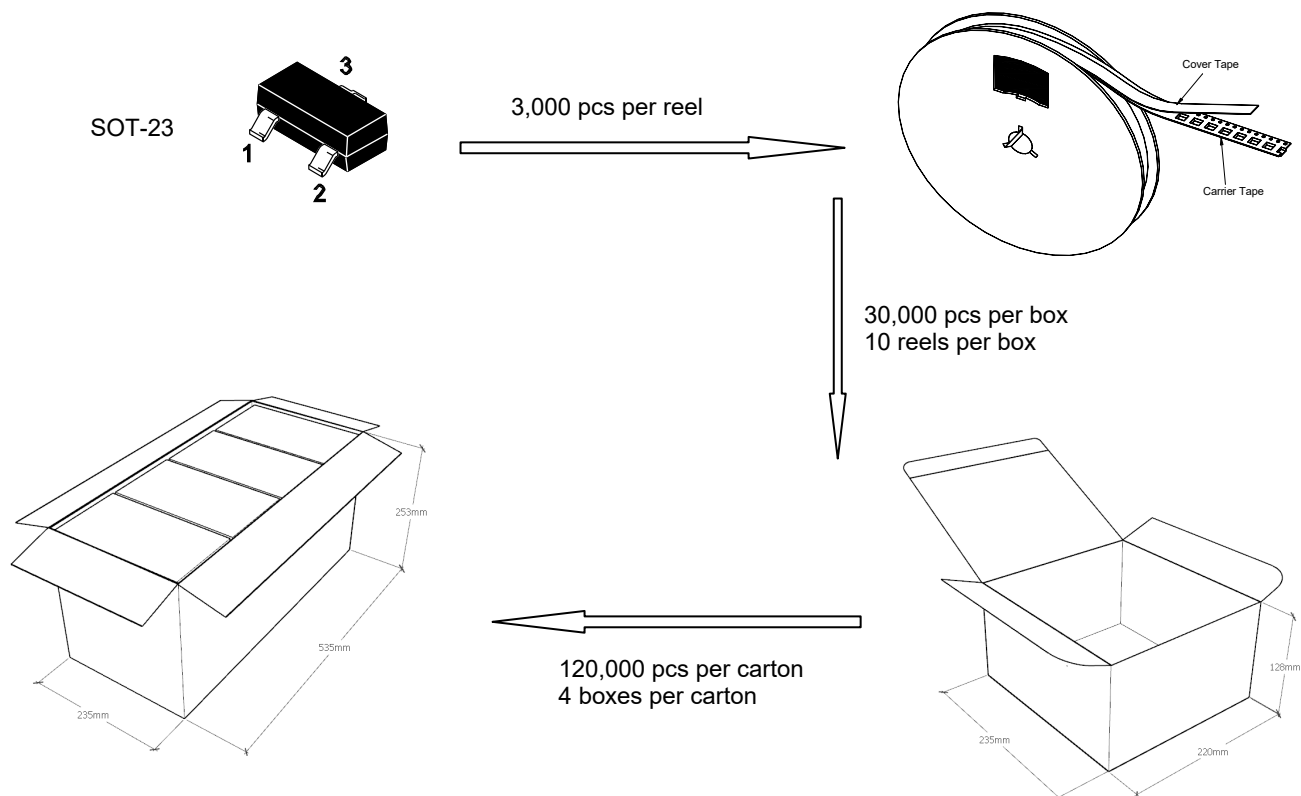
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

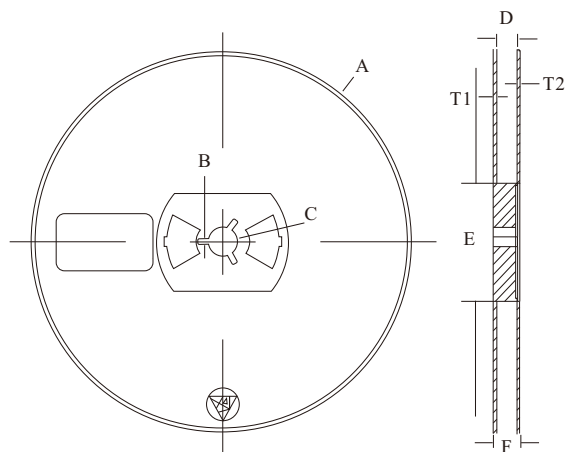
- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing

Package Specifications

- The method of packaging



◆ Embossed tape and reel data



Reel (7")

Symbol	Value (unit: mm)
A	$\varnothing 177.8 \pm 1$
B	2.7 ± 0.2
C	$\varnothing 13.5 \pm 0.2$
E	$\varnothing 54.5 \pm 0.2$
F	12.3 ± 0.3
D	$9.6 \pm 2 / -0.3$
T1	1.0 ± 0.2
T2	1.2 ± 0.2

